

TECHNICAL DATA DATA SHEET 1049, REV. –

HERMETIC POWER SCHOTTKY RECTIFIER

200°C Maximum Operation Temperature Very Low Forward Voltage Drop

Applications:

• Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

Features:

- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Reverse Leakage Current
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

MAXIMUM RATINGS

ALL RATINGS ARE @ $T_C = 25$ °C UNLESS OTHERWISE SPECIFIED.

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RATING	SYMBOL	MAX.	UNITS
PEAK INVERSE VOLTAGE	PIV	200	Volts
MAXIMUM DC OUTPUT CURRENT (With Cathode Maintained @ $T_C=100$ $^{\circ}$ C)	Io	60	Amps
MAXIMUM NONREPETITIVE FORWARD SURGE CURRENT (t=8.3ms, Sine)	I _{FSM}	860	Amps
MAXIMUM THERMAL RESISTANCE (Junction to Mounting Surface, Cathode)	$R_{ hetaJC}$	0.35	°C/W
MAXIMUM OPERATING AND STORAGE TEMPERATURE RANGE	Top/Tstg	-65 to + 200	°C
MAXIMUM STORAGE TEMPERATURE RANGE	Top/Tstg	-65 to + 175	°C

ELECTRICAL CHARACTERISTICS

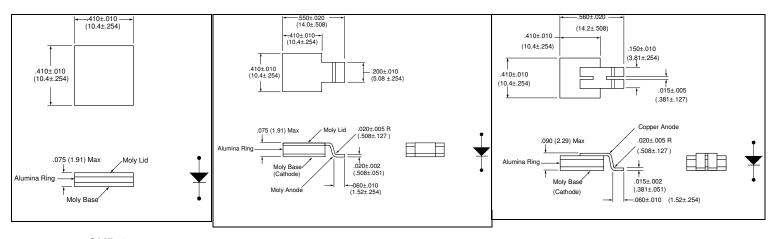
CHARACTERISTIC	SYMBOL	MAX.	UNITS
MAXIMUM FORWARD VOLTAGE DROP, Pulsed (I _f = 60 Amps)			
$T_J = 25 ^{\circ}\text{C}$ $T_J = 125 ^{\circ}\text{C}$	V_{f}	0.95 0.79	Volts
MAXIMUM REVERSE CURRENT (I _r @ 200V PIV)			
$T_J = 25 ^{\circ}\text{C}$ $T_J = 125 ^{\circ}\text{C}$	l _r	1.1 24	mA
MAXIMUM JUNCTION CAPACITANCE (V _r =	5V) C _T	900	рF

^{*}Due to the nature of the 200V Schottky devices, some degradation in t_{rr} performance at high temperatures should be expected, unlike conventional lower voltage Schottkys.

SENSITRON

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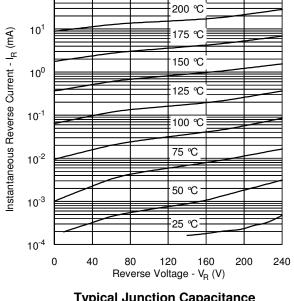
MECHANICAL DIMENSIONS: In Inches / mm

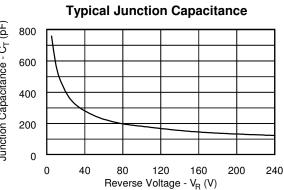


SHD-3A SHD-3B

Typical Forward Characteristics 10^{2} Instantaneous Reverse Current - IR (mA) 200 ℃ 10¹ 175 °C Instantaneous Forward Current - $I_{\rm F}$ (A) 10⁰ 125 °C Junction Capacitance - C_T (pF) 25 ℃ 10⁻¹ 10⁻² 0.6 1.0 0.0 0.4 8.0 Forward Voltage Drop - V_F (V)

Typical Reverse Characteristics







TECHNICAL DATA

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